COMPLEMENTARY SILICON POWER TRANSISTORS

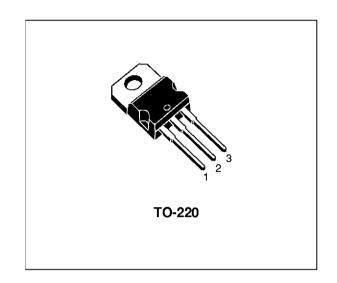
■ SGS-THOMSON PREFERRED SALESTYPES

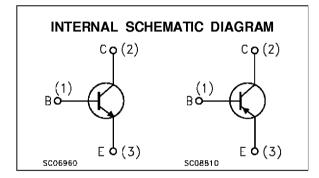
DESCRIPTION

The BD241A, BD241B and BD241C are silicon epitaxial-base NPN transistors mounted in Jedec TO-220 plastic package.

They are inteded for use in medium power linear and switching applications.

The complementary PNP types are BD242A, BD242B and BD242C respectively.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value		Unit
		NPN	BD241A	BD241B	BD241C	
		PNP	BD242A	BD242B	BD242C]
V _{CER}	Collector-Base Voltage ($R_{BE} = 100 \Omega$)		70	90	115	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		60	80	100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)			5		V
Ic	Collector Current			3		Α
I _{CM}	Collector Peak Current			5		Α
I _B	Base Current			1		Α
P _{tot}	Total Dissipation at T _c ≤ 25 °C			40		W
P _{tot}	Total Dissipation at T _{amb} ≤ 25 °C			2		W
T _{stg}	Storage Temperature			-65 to 150		°C
Tj	Max. Operating Junction Temperature			150		°C

For PNP types voltage and current values are negative.

October 1995 1/4

THERMAL DATA

	R _{thj-case}	Thermal	Resistance	Junction-case	Max	3.13	°C/W
١	R _{thj-amb}	Thermal	Resistance	Junction-ambient	Max	62.5	°C/W

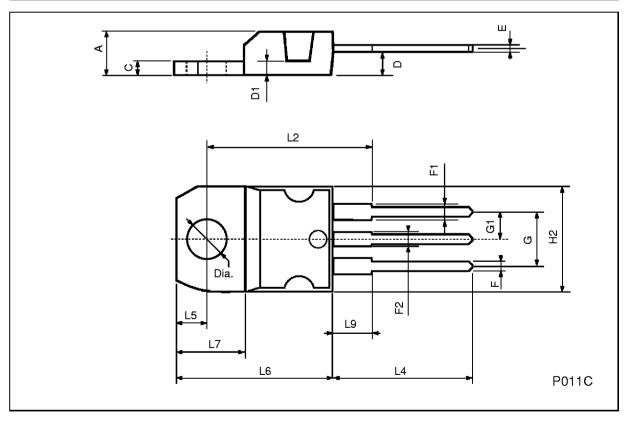
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = rated V _{CEO}			0.2	m A
I _{CEO}	Collector Cut-off Current (I _B = 0)	for BD241A/BD242A			0.3 0.3 0.3	mA mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	m A
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage	I _C = 30 mA for BD241A/BD242A for BD241B/BD242B for BD241C/BD242C	60 80 100			<<<
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	Ic = 3 A I _B = 0.6 A			1.2	V
V _{BE} *	Base-Emitter Voltage	Ic = 3 A VcE = 4 V			1.8	\ \
h _{FE} *	DC Current Gain	Ic = 1 A	25 10			
h _{fe}	Small Signal Current Gain	I _C = 0.5 A V _{CE} = 10 V f = 1MHz I _C = 0.5 A V _{CE} = 10 V f = 1KHz	3 20			

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 % For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	4.40		4.60	0.173		0.181	
С	1.23		1.32	0.048		0.051	
D	2.40		2.72	0.094		0.107	
D1		1.27			0.050		
Е	0.49		0.70	0.019		0.027	
F	0.61		0.88	0.024		0.034	
F1	1.14		1.70	0.044		0.067	
F2	1.14		1.70	0.044		0.067	
G	4.95		5.15	0.194		0.203	
G1	2.4		2.7	0.094		0.106	
H2	10.0		10.40	0.393		0.409	
L2		16.4			0.645		
L4	13.0		14.0	0.511		0.551	
L5	2.65		2.95	0.104		0.116	
L6	15.25		15.75	0.600		0.620	
L7	6.2		6.6	0.244		0.260	
L9	3.5		3.93	0.137		0.154	
DIA.	3.75		3.85	0.147		0.151	



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

@ 1995 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectrorics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

STMicroelectronics: BD242B